



DFNWB3x3-8L Plastic-Encapsulate MOSFETS

AE10P06 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
-60V	26mΩ@-10V	-10A



DESCRIPTION

The AE10P06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

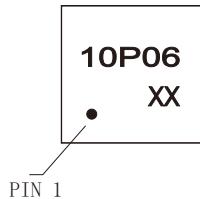
FEATURES

- Battery switch
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Fully characterized avalanche voltage and current

APPLICATIONS

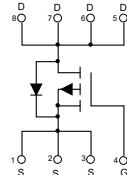
- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING



10P06=Part No.
Solid dot=Pin1 indicator.
XX=Code.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D ^①	-10	A
Pulsed Drain Current	I_{DM} ^②	-40	A
Single Pulsed Avalanche Energy	E_{AS} ^③	180	mJ
Power Dissipation	P_D ^①	30.5	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$ ^①	4.1	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$ ^⑥	83.3	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

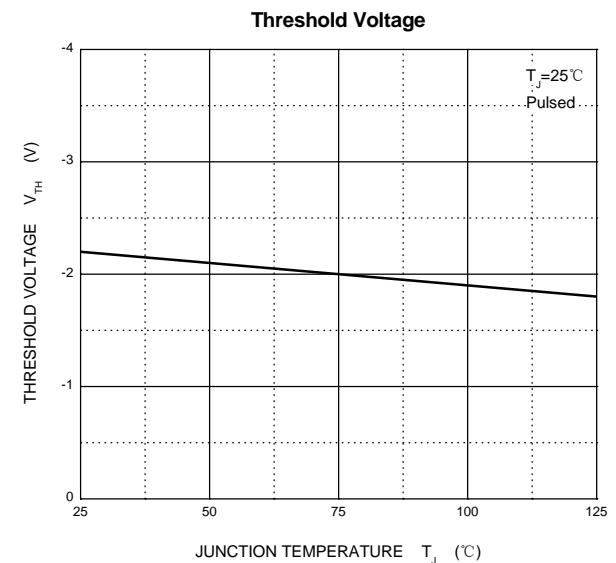
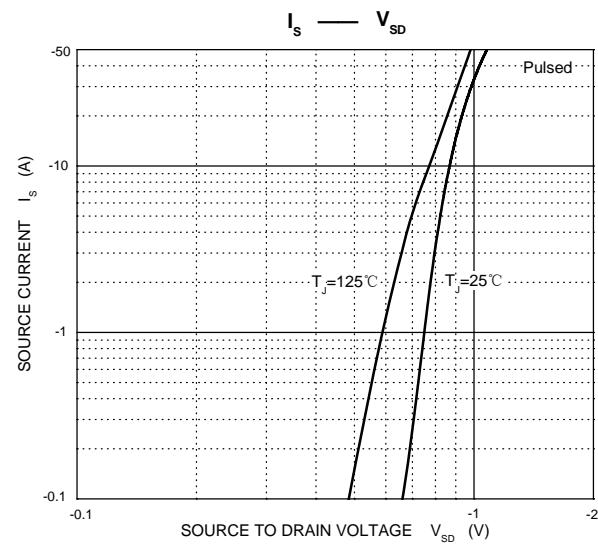
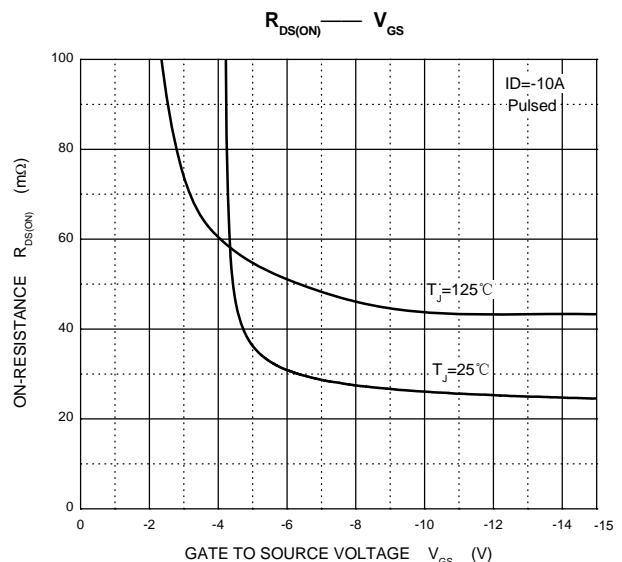
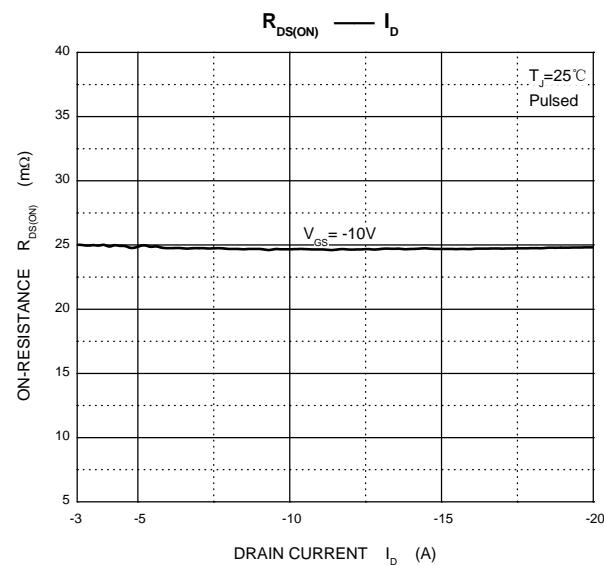
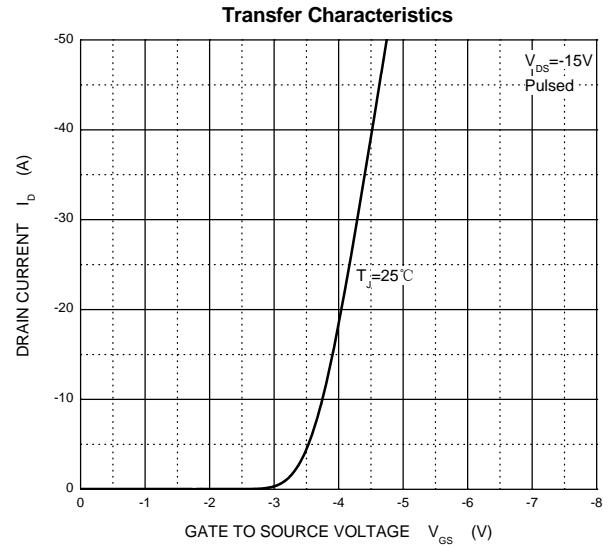
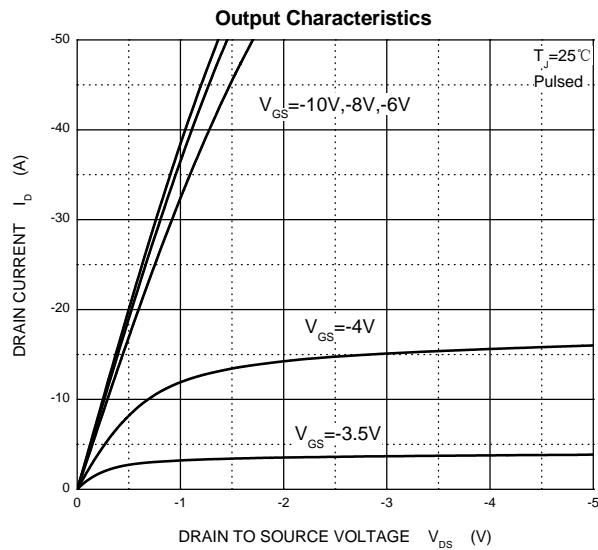
$T_a=25^\circ C$ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$		-60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	$T_J = 25^\circ C$			1	μA
			$T_J = 125^\circ C$			300	
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$				± 100	nA
On characteristics ^④							
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$		-1.0	-2.2	-3.0	V
Static drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$			26	35	$m\Omega$
Dynamic characteristics ^{④ ⑤}							
Input capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$			4500		pF
Output capacitance	C_{oss}				705		
Reverse transfer capacitance	C_{rss}				515		
Gate resistance	R_g	$f = 1MHz$			6.0		Ω
Switching characteristics ^{④ ⑤}							
Total gate charge	Q_g	$V_{GS} = -10V, V_{DS} = -30V, I_D = -10A$			52		nC
Gate-source charge	Q_{gs}				12		
Gate-drain charge	Q_{gd}				15		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -30V, R_G = 3\Omega, R_L = 1.5\Omega, V_{GS} = -10V$			16		ns
Turn-on rise time	t_r				18		
Turn-off delay time	$t_{d(off)}$				39		
Turn-off fall time	t_f				44		
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V_{SD} ^④	$V_{GS} = 0V, I_S = -1A$				-1.2	V
Continuous drain-source diode forward current	I_S ^①					-10	A
Pulsed drain-source diode forward current	I_{SM} ^②					-40	A

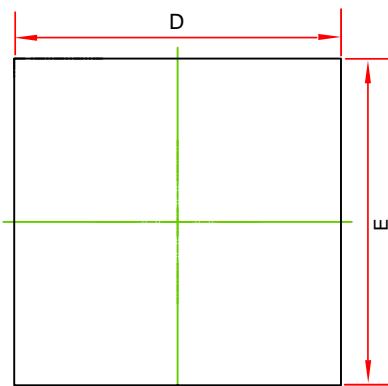
Notes:

1. $T_c = 25^\circ C$ Limited only by maximum temperature allowed.
2. $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$.
3. EAS condition: $V_{DD} = -15V, V_{GS} = -10V, L = 0.5mH, R_g = 25\Omega$ Starting $T_J = 25^\circ C$.
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. Guaranteed by design, not subject to production.
6. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25^\circ C$. $t \leq 10sec$.

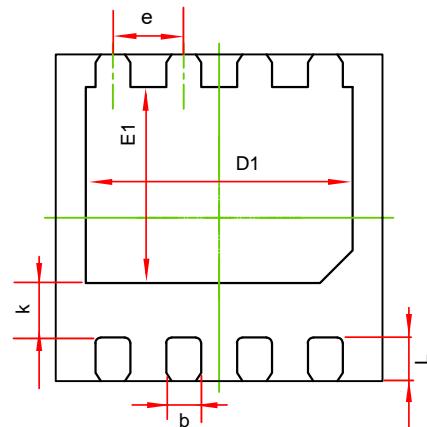
Typical Characteristics



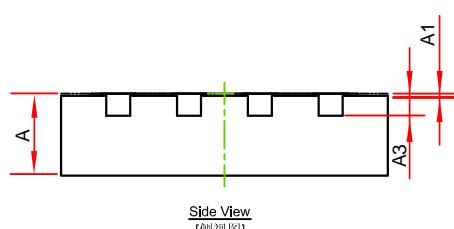
DFNWB3×3-8L Package Outline Dimensions



Top View
[顶视图]



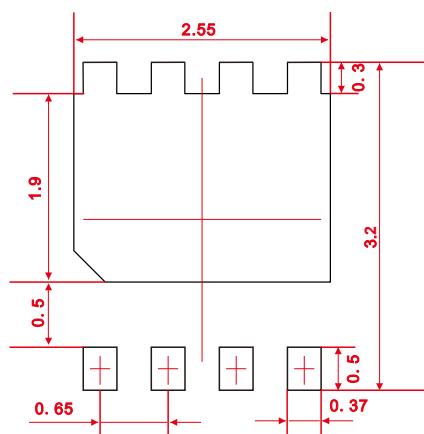
Bottom View
[底视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203 REF.		0.008 REF.	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.350	2.550	0.093	0.100
E1	1.700	1.900	0.067	0.075
k	0.200 MIN.		0.008 MIN.	
b	0.270	0.370	0.011	0.015
e	0.650 TYP.		0.026 TYP.	
L	0.300	0.500	0.012	0.020

DFNWB3×3-8L Suggested Pad Layout

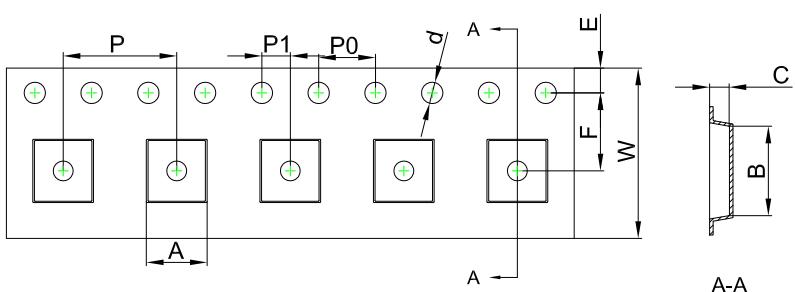


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

DFNWB3x3-8L Tape and Reel

DFNWB3x3-8L Embossed Carrier Tape



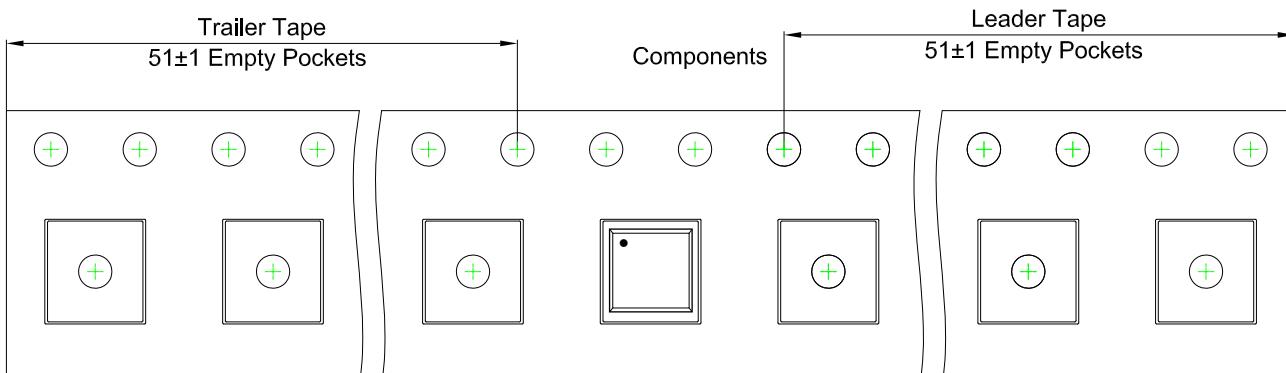
Packaging Description:

DFNWB3x3-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

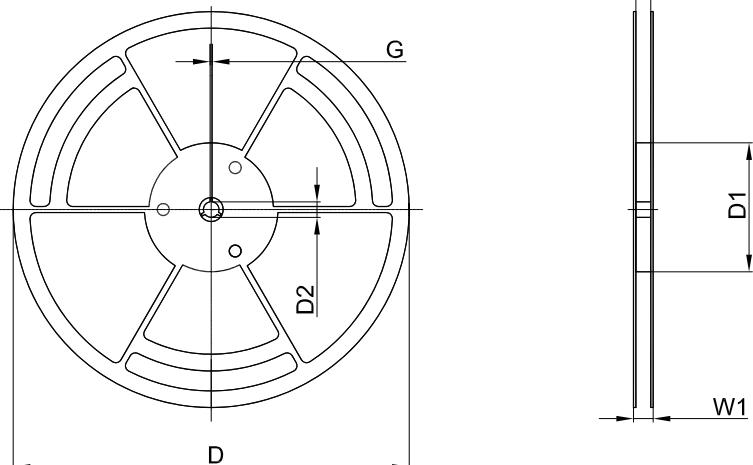
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
DFNWB3x3-8L	3.35	3.35	1.13	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

DFNWB3x3-8L Tape Leader and Trailer



DFNWB3x3-8L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	W1	W2
13" Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	10,000 pcs	360×360×65	50,000 pcs	378×358×382